

# **BC847BS**

# 45 V, 100 mA NPN/NPN general-purpose transistor Rev. 03 — 18 February 2009 Produ

**Product data sheet** 

### 1. Product profile

### 1.1 General description

NPN/NPN general-purpose transistor pair in a very small SOT363 (SC-88) Surface-Mounted Device (SMD) plastic package.

PNP/PNP complement: BC857BS.

#### 1.2 Features

- Low collector capacitance
- Low collector-emitter saturation voltage
- Closely matched current gain
- Reduces number of components and board space
- No mutual interference between the transistors

### 1.3 Applications

■ General-purpose switching and amplification

#### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per trans	istor					
$V_{CEO}$	collector-emitter voltage	open base	-	-	45	V
I <sub>C</sub>	collector current		-	-	100	mA
h <sub>FE</sub>	DC current gain	$V_{CE} = 5 \text{ V}; I_{C} = 2 \text{ mA}$	200	-	450	



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### 2. Pinning information

Table 2. Pinning

Table 2.	rilling		
Pin	Description	Simplified outline	Graphic symbol
1	emitter TR1		0 5 4
2	base TR1		6 5 4
3	collector TR2		TR2
4	emitter TR2	0	(TR1)
5	base TR2	□1 □2 □3	
6	collector TR1		1 2 3
			sym020

## 3. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
BC847BS	SC-88	plastic surface-mounted package; 6 leads	SOT363		

### 4. Marking

Table 4. Marking codes

Type number	Marking code <sup>[1]</sup>
BC847BS	1F*

- [1] \* = -: made in Hong Kong
  - \* = p: made in Hong Kong
  - \* = t: made in Malaysia
  - \* = W: made in China

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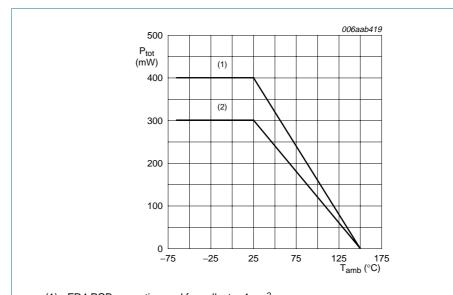
### 5. Limiting values

**Table 5.** Limiting values
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Per transis	stor				
$V_{CBO}$	collector-base voltage	open emitter	-	50	V
$V_{CEO}$	collector-emitter voltage	open base	-	45	V
$V_{EBO}$	emitter-base voltage	open collector	-	5	V
$I_{C}$	collector current		-	100	mA
I <sub>CM</sub>	peak collector current	single pulse; $t_p \le 1 \text{ ms}$	-	200	mA
$I_{BM}$	peak base current	single pulse; $t_p \le 1 \text{ ms}$	-	200	mA
P <sub>tot</sub>	total power dissipation	$T_{amb} \le 25  ^{\circ}C$	[1] -	220	mW
			[2] -	250	mW
Per device					
P <sub>tot</sub>	total power dissipation	$T_{amb} \le 25  ^{\circ}C$	[1] -	300	mW
			[2] -	400	mW
Tj	junction temperature		-	150	°C
T <sub>amb</sub>	ambient temperature		-65	+150	°C
T <sub>stg</sub>	storage temperature		-65	+150	°C

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.



<sup>(1)</sup> FR4 PCB, mounting pad for collector 1 cm<sup>2</sup>

Fig 1. Per device: Power derating curves SOT363 (SC-88)

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<sup>(2)</sup> FR4 PCB, standard footprint

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### 6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transist	or						
R <sub>th(j-a)</sub> thermal resistance find junction to ambient	thermal resistance from		<u>[1]</u>	-	-	568	K/W
	junction to ambient		[2]	-	-	500	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	-	230	K/W
Per device							
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	<u>[1]</u>	-	-	416	K/W
			[2]	-	-	313	K/W

<sup>[1]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

<sup>[2]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.

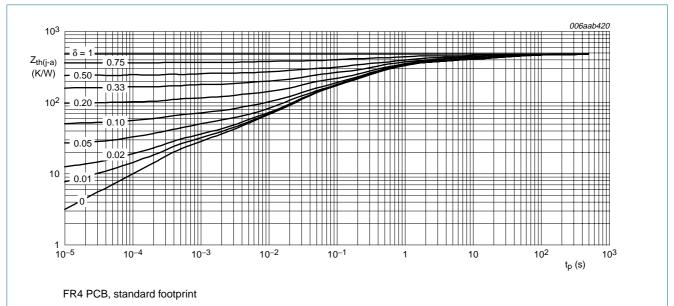
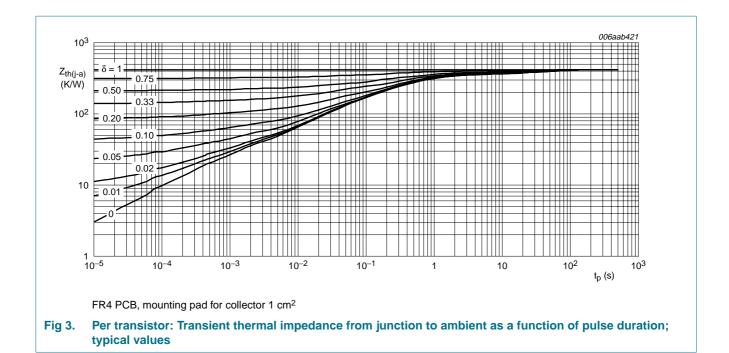


Fig 2. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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### 7. Characteristics

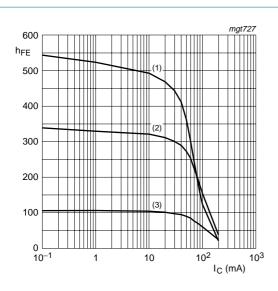
Table 7. Characteristics

 $T_{amb}$  = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per trans	Per transistor					
$I_{CBO}$	collector-base cut-off	$V_{CB} = 30 \text{ V}; I_E = 0 \text{ A}$	-	-	15	nA
	current	$V_{CB} = 30 \text{ V; } I_{E} = 0 \text{ A;}$ $T_{j} = 150 ^{\circ}\text{C}$	-	-	5	μΑ
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; I_{C} = 0 \text{ A}$	-	-	100	nA
h <sub>FE</sub>	DC current gain	$V_{CE} = 5 \text{ V}; I_{C} = 2 \text{ mA}$	200	-	450	
V <sub>CEsat</sub>	collector-emitter	$I_C = 10 \text{ mA}; I_B = 0.5 \text{ mA}$	-	-	100	mV
	saturation voltage	$I_C = 100 \text{ mA}; I_B = 5 \text{ mA}$	[1] -	-	300	mV
$V_{BEsat}$	base-emitter saturation voltage	$I_C = 10 \text{ mA}; I_B = 0.5 \text{ mA}$	-	755	-	mV
$V_{BE}$	base-emitter voltage	$I_C = 2 \text{ mA}$ ; $V_{CE} = 5 \text{ V}$	580	655	700	mV
C <sub>c</sub>	collector capacitance	$I_E = i_e = 0 \text{ A}; V_{CB} = 10 \text{ V};$ f = 1 MHz	-	-	1.5	pF
C <sub>e</sub>	emitter capacitance	$I_C = I_c = 0 \text{ A}; V_{EB} = 0.5 \text{ V};$ f = 1 MHz	-	11	-	pF
f <sub>T</sub>	transition frequency	$I_C = 10 \text{ mA}; V_{CE} = 5 \text{ V};$ f = 100 MHz	100	-	-	MHz

<sup>[1]</sup> Pulse test:  $t_p \le 300 \ \mu s; \ \delta \le 0.02$ .

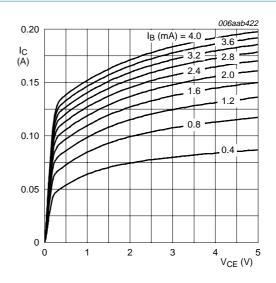
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$$V_{CE} = 5 V$$

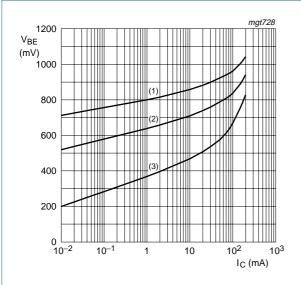
- (1)  $T_{amb} = 150 \, ^{\circ}C$
- (2)  $T_{amb} = 25 \, ^{\circ}C$
- (3)  $T_{amb} = -55 \,^{\circ}C$

Fig 4. Per transistor: DC current gain as a function of collector current; typical values



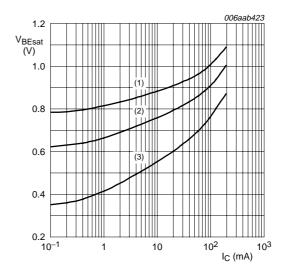
 $T_{amb} = 25 \, ^{\circ}C$ 

Fig 5. Per transistor: Collector current as a function of collector-emitter voltage; typical values



- $V_{CE} = 5 V$
- (1)  $T_{amb} = -55 \, ^{\circ}C$
- (2)  $T_{amb} = 25 \, ^{\circ}C$
- (3)  $T_{amb} = 150 \, ^{\circ}C$

Fig 6. Per transistor: Base-emitter voltage as a function of collector current; typical values



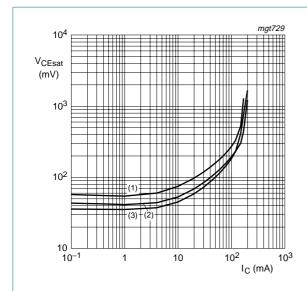
 $I_{\rm C}/I_{\rm B} = 20$ 

- (1)  $T_{amb} = -55$  °C
- (2)  $T_{amb} = 25 \, ^{\circ}C$
- (3)  $T_{amb} = 150 \, ^{\circ}C$

Fig 7. Per transistor: Base-emitter saturation voltage as a function of collector current; typical values

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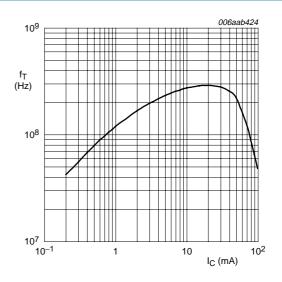
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$$I_{\rm C}/I_{\rm B} = 20$$

- (1)  $T_{amb} = 150 \, ^{\circ}C$
- (2)  $T_{amb} = 25 \, ^{\circ}C$
- (3)  $T_{amb} = -55 \, ^{\circ}C$

Fig 8. Per transistor: Collector-emitter saturation voltage as a function of collector current; typical values

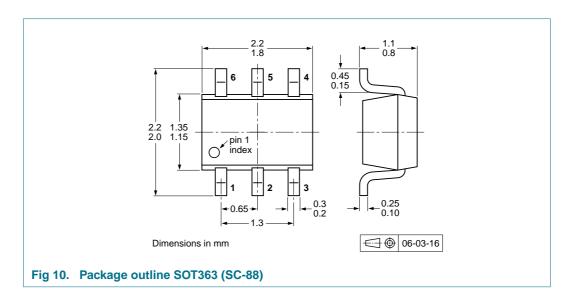


 $V_{CE}$  = 5 V; f = 1 MHz;  $T_{amb}$  = 25 °C

Fig 9. Per transistor: Transition frequency as a function of collector current; typical values

### 45 V, 100 mA NPN/NPN general-purpose transistor

### 8. Package outline



### 9. Packing information

Table 8. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description		Packing quantity	
				3000	10000
BC847BS	SOT363	4 mm pitch, 8 mm tape and reel; T1	[2]	-115	-135
		4 mm pitch, 8 mm tape and reel; T2	[3]	-125	-165

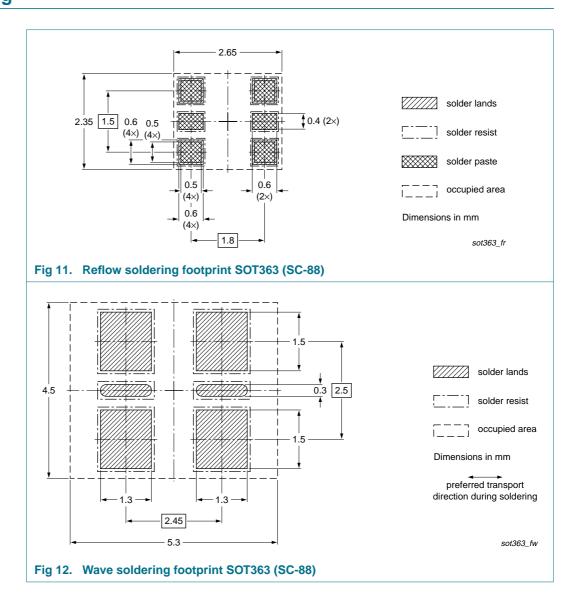
<sup>[1]</sup> For further information and the availability of packing methods, see Section 13.

<sup>[2]</sup> T1: normal taping

<sup>[3]</sup> T2: reverse taping

### 45 V, 100 mA NPN/NPN general-purpose transistor

### 10. Soldering



### 45 V, 100 mA NPN/NPN general-purpose transistor

# 11. Revision history

### Table 9. Revision history

Release date	Data sheet status	Change notice	Supersedes		
20090218	Product data sheet	-	BC847BS_2		
<ul> <li>The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors.</li> </ul>					
<ul> <li>Legal texts have been adapted to the new company name where appropriate.</li> <li>Section 4 "Marking": updated</li> </ul>					
				<ul> <li>Section 7 "Char</li> </ul>	racteristics": enhanced
<ul> <li>Section 9 "Packing information": added</li> </ul>					
<ul> <li>Section 10 "Sol</li> </ul>	dering": added				
<ul> <li>Section 12 "Leg</li> </ul>	gal information": updated				
19990428	Product specification	-	BC847BS_1		
19970714	Product specification	-	-		
	The format of the of NXP Semico Legal texts have Section 4 "Mark Section 7 "Chart Section 9 "Pack Section 10 "Sol Section 12 "Legal 19990428	<ul> <li>The format of this data sheet has been rede of NXP Semiconductors.</li> <li>Legal texts have been adapted to the new of Section 4 "Marking": updated</li> <li>Section 7 "Characteristics": enhanced</li> <li>Section 9 "Packing information": added</li> <li>Section 10 "Soldering": added</li> <li>Section 12 "Legal information": updated</li> </ul>	Product data sheet  The format of this data sheet has been redesigned to comply with of NXP Semiconductors.  Legal texts have been adapted to the new company name where  Section 4 "Marking": updated  Section 7 "Characteristics": enhanced  Section 9 "Packing information": added  Section 10 "Soldering": added  Section 12 "Legal information": updated  Product specification  -		

#### 45 V, 100 mA NPN/NPN general-purpose transistor

### 12. Legal information

#### 12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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